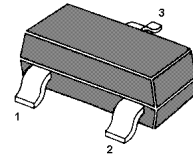


# MMBTA6571

## PNP Silicon Epitaxial Planar Transistor

for general amplifier applications.



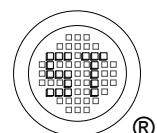
1. Base 2. Emitter 3. Collector  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	7	V
Collector Current	$-I_C$	100	mA
Peak Collector Current	$-I_{CP}$	200	mA
Power Dissipation	$P_{tot}$	350	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ	Max.	Unit	
DC Current Gain at $-V_{CE} = 10\text{ V}$ , $-I_C = 2\text{ mA}$ Current Gain Group	Q	$h_{FE}$	160	-	260	-
	R	$h_{FE}$	210	-	340	-
	S	$h_{FE}$	290	-	460	-
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	-	10	nA	
Collector Emitter Cutoff Current at $-V_{CE} = 50\text{ V}$	$-I_{CEO}$	-	-	100	$\mu\text{A}$	
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	10	nA	
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	60	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	7	-	-	V	
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$ , $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V	
Current Gain Bandwidth Product at $-V_{CB} = 10\text{ V}$ , $I_E = 1\text{ mA}$ , $f = 200\text{ MHz}$	$f_T$	-	80	-	MHz	
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	2.7	-	pF	



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